Thank you for your interest in onsemi products.

Your technical document begins on the following pages.



# Your Feedback is Important to Us!

Please take a moment to participate in our short survey.

At **onsemi**, we are dedicated to delivering technical content that best meets your needs.

# Help Us Improve - Take the Survey

This survey is intended to collect your feedback, capture any issues you may encounter, and to provide improvements you would like to suggest.

We look forward to your feedback.

To learn more about **onsemi**, please visit our website at **www.onsemi.com** 

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributor



# **MOSFET** - N-Channel, **Small Signal, SOT-23**

# 60 V, 115 mA

# 2N7002L, 2V7002L

#### **Features**

- 2V Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable (2V7002L)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	Vdc
Drain-Gate Voltage ( $R_{GS}$ = 1.0 $M\Omega$ )	$V_{DGR}$	60	Vdc
Drain Current  - Continuous $T_C = 25^{\circ}C$ (Note 1) $T_C = 100^{\circ}C$ (Note 1)  - Pulsed (Note 2)	I <sub>D</sub> I <sub>D</sub> I <sub>DM</sub>	±115 ±75 ±800	mAdc
Gate-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk

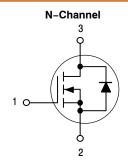
### THERMAL CHARACTERISTICS

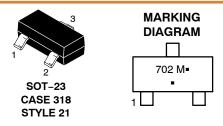
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) T <sub>A</sub> = 25°C Derate above 25°C Thermal Resistance, Junction-to-Ambient	$P_D$	225 1.8 556	mW mW/°C °C/W
Total Device Dissipation (Note 4) Alumina Substrate, T <sub>A</sub> = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	$P_D$	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.
- 3.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 4. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX
60 V	7.5 Ω @ 10 V, 500 mA	115 mA





702 = Device Code = Date Code\* = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
2N7002LT1G		3,000 Tape & Reel
2N7002LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
2N7002LT7G		3,500 Tape & Reel
2V7002LT1G		3,000 Tape & Reel
2V7002LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
2N7002LT1H*		3,000 Tape & Reel
2N7002LT7H*		3,500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

<sup>\*</sup>Not for new design.

## 2N7002L, 2V7002L

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•
Drain–Source Breakdown Voltage $(V_{GS} = 0, I_D = 10 \mu Adc)$	V <sub>(BR)DSS</sub>	60	_	-	Vdc
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$ $(V_{GS} = 0, V_{DS} = 60 \text{ Vdc})$ $T_J = 125^{\circ}C$	I <sub>DSS</sub>	- -	- -	1.0 500	μAdc
Gate-Body Leakage Current, Forward (V <sub>GS</sub> = 20 Vdc)	I <sub>GSSF</sub>	_	_	100	nAdc
Gate-Body Leakage Current, Reverse (V <sub>GS</sub> = -20 Vdc)	I <sub>GSSR</sub>	-	_	-100	nAdc
ON CHARACTERISTICS (Note 5)					
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250 \mu Adc$ )	V <sub>GS(th)</sub>	1.0	_	2.5	Vdc
On–State Drain Current $(V_{DS} \ge 2.0 \ V_{DS(on)}, \ V_{GS} = 10 \ Vdc)$	I <sub>D(on)</sub>	500	_	-	mA
Static Drain–Source On–State Voltage $(V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAdc})$ $(V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc})$	V <sub>DS(on)</sub>	- -	- -	3.75 0.375	Vdc
$\label{eq:static} \begin{array}{ll} \text{Static Drain-Source On-State Resistance} \\ (V_{GS} = 10 \text{ V, } I_D = 500 \text{ mAdc}) & T_C = 25^{\circ}\text{C} \\ T_C = 125^{\circ}\text{C} & \\ (V_{GS} = 5.0 \text{ Vdc, } I_D = 50 \text{ mAdc}) & T_C = 25^{\circ}\text{C} \\ T_C = 125^{\circ}\text{C} & \\ \end{array}$	r <sub>DS(on)</sub>	- - - -	- - - -	7.5 13.5 7.5 13.5	Ohms
Forward Transconductance ( $V_{DS} \ge 2.0 \ V_{DS(on)}$ , $I_D = 200 \ mAdc$ )	9FS	80	_	-	mS
DYNAMIC CHARACTERISTICS			•	•	
Input Capacitance ( $V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$ )	C <sub>iss</sub>	-	_	50	pF
Output Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>oss</sub>	-	_	25	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>rss</sub>	-	_	5.0	pF
SWITCHING CHARACTERISTICS (Note 5)					
Turn–On Delay Time $(V_{DD} = 25 \text{ Vdc}, I_{D} \cong 500 \text{ mAdc},$	t <sub>d(on)</sub>	-	_	20	ns
Turn–Off Delay Time $R_G = 25 \Omega$ , $R_L = 50 \Omega$ , $V_{gen} = 10 V$ )	t <sub>d(off)</sub>		-	40	ns
BODY-DRAIN DIODE RATINGS					
Diode Forward On-Voltage (I <sub>S</sub> = 115 mAdc, V <sub>GS</sub> = 0 V)	V <sub>SD</sub>	-	_	-1.5	Vdc
Source Current Continuous (Body Diode)	I <sub>S</sub>	-	_	-115	mAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

## 2N7002L, 2V7002L

### TYPICAL ELECTRICAL CHARACTERISTICS

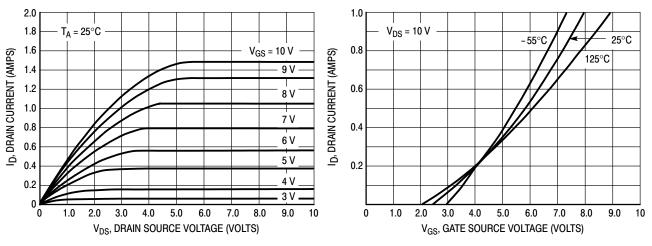


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

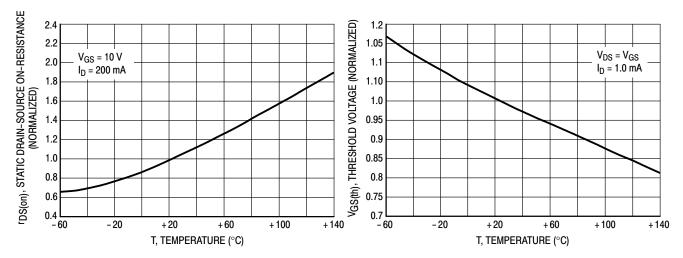


Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

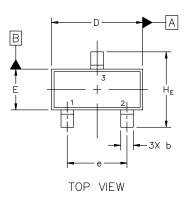
2.04

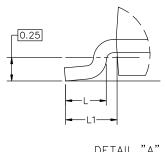
0.55

0.69

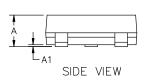
2.64

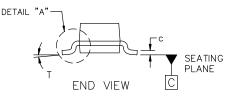
10°

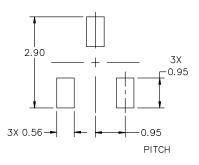




DETAIL "A" Scale 3:1







### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2	

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries, onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR		NODE D CONNECTION ATHODE	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11:         STYLE 12:           PIN 1. ANODE         PIN 1. CA           2. CATHODE         2. CA           3. CATHODE-ANODE         3. AN	ATHODE PIN 1. SOURCE ATHODE 2. DRAIN	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE			STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23:         STYLE 24:           PIN 1. ANODE         PIN 1. GAT           2. ANODE         2. DR/           3. CATHODE         3. SOU	TE PIN 1. ANODE AIN 2. CATHODE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales